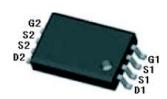




### N-Channel 20V,18mΩ max, Power MOSFET

	<b>Product Summary</b>							
-	V <sub>DS</sub> (V)	R <sub>DS(on),max</sub> (mΩ)	I <sub>D</sub> (A)					
	20	18 @ V <sub>GS</sub> = 4.5V	7					

### **View and Internal Schematic Diagram**



TSSOP-8

ÞUVÒKÁ ŠUÕUÆÄÕS GMT180D02B1 Part number code ØÆÄØæàÁ[&æaā]}ÁS[å^Á ήÄQE•^{{à|^Á|&æaā}}Æ[å^Á ŸÆÄY^æÁS[å^Á Y WÆÄY^^\Æ[å^Á ŠBVÆÄØE•^{{à|^Á|}øÆ[å^

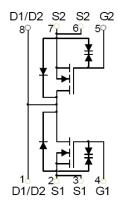
#### **Features**

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### **Application**

- Uni-directional load switch
- Bi-directional load switch

### **Equivalent circuit**



## Absolute maximum rating@25℃

Parameter	Symbol	Limit	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GS</sub>	±12	V
Continuous drain current (V <sub>GS</sub> =-4.5V) T <sub>A</sub> =25°C	I <sub>D</sub>	7	Α
Pulsed drain current <sup>(d)</sup>	I <sub>D,pulse</sub>	30	Α
Power dissipation T <sub>A</sub> =25°C	P <sub>D</sub>	2	W
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

### **Thermal Characteristic**

Parameter	Symbol	Тур.	Max.	Unit
Thermal Resistance, Junction-to-Ambient (C)	R <sub>θJA</sub>	62.5		°C/W



# Electrical Characteristics (TJ=25℃ unless otherwise noted)

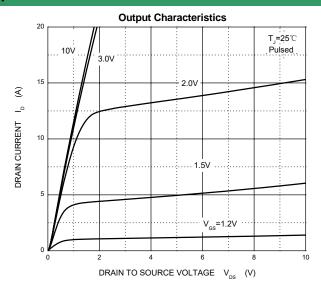
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static <sup>a</sup>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.5	0.7	1.0	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
Drain-Source On-State Resistance	R	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5 A		14	18	mΩ	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3A		17	22	mΩ	
Forward Transconductancea	9 <sub>fs</sub>	$V_{DS} = 5 \text{ V}, I_{D} = 8 \text{ A}$		15		S	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		0.8	1.2	٧	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			555		pF	
Output Capacitance	Coss	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		130			
Reverse Transfer Capacitance	C <sub>rss</sub>			90		1	
Total Gate Charge	Qg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A		17			
Gate-Source Charge	Q <sub>gs</sub>	$v_{DS} = 10 \text{ V}, v_{GS} = 4.5 \text{ V}, v_{D} = 6 \text{ A}$		1.2		nC	
Gate-Drain Charge	Q <sub>gd</sub>			3.7		1	
Turn-On Delay Time	t <sub>d(on)</sub>			5.5			
Rise Time	t <sub>r</sub>	$V_{DS} = 10 \text{ V}, R_{L} = 1.2 \Omega$		12		]	
Turn-Off Delay Time	t <sub>d(off)</sub>	Vgs= 5 V, $R_{gen}$ = 3 $\Omega$		49		ns	
Fall Time	t <sub>f</sub>			14.8			

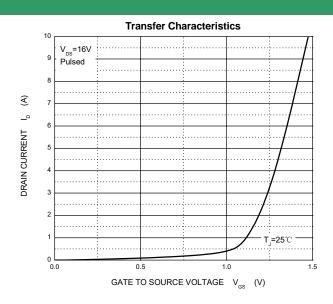
#### Notes

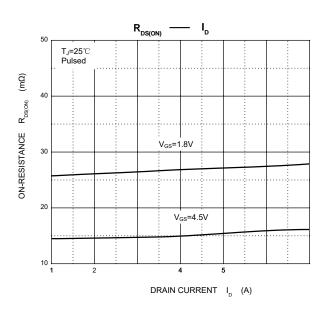
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Surface Mounted on FR4 Board, t ≤10 sec.
- d. Repetitive Rating: Pulse width limited by maximum junction temperature.

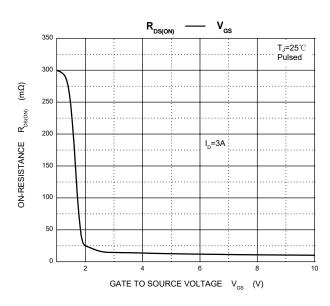


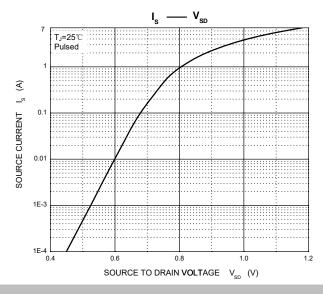
## **Typical Performance Characteristics**

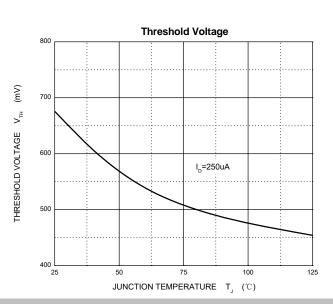








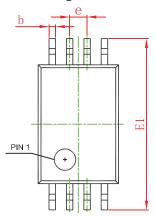


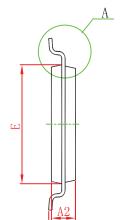


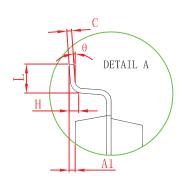


# **Outline Drawing SOP-8**

## Package Outline: TSSOP-8









Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibor	Min	Max	Min	Max	
D	2. 900	3. 100	0.114	0.122	
Е	4.300	4. 500	0. 169	0.177	
b	0. 190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6. 250	6. 550	0. 246	0. 258	
A		1. 200		0.047	
A2	0.800	1.000	0. 031	0.039	
A1	0.050	0. 150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TY	P .	0.01(TYP		
θ	1°	7°	1°	7°	



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